

MC33078, MC33079

Dual/Quad Low Noise Operational Amplifiers

The MC33078/9 series is a family of high quality monolithic amplifiers employing Bipolar technology with innovative high performance concepts for quality audio and data signal processing applications. This family incorporates the use of high frequency PNP input transistors to produce amplifiers exhibiting low input voltage noise with high gain bandwidth product and slew rate. The all NPN output stage exhibits no deadband crossover distortion, large output voltage swing, excellent phase and gain margins, low open loop high frequency output impedance and symmetrical source and sink AC frequency performance.

The MC33078/9 family offers both dual and quad amplifier versions, tested over the automotive temperature range and available in the plastic DIP and SOIC packages (P and D suffixes).

- Dual Supply Operation: ± 5.0 V to ± 18 V
- Low Voltage Noise: $4.5 \text{ nV}/\sqrt{\text{Hz}}$
- Low Input Offset Voltage: 0.15 mV
- Low T.C. of Input Offset Voltage: $2.0 \mu\text{V}/^\circ\text{C}$
- Low Total Harmonic Distortion: 0.002%
- High Gain Bandwidth Product: 16 MHz
- High Slew Rate: 7.0 V/ μs
- High Open Loop AC Gain: 800 @ 20 kHz
- Excellent Frequency Stability
- Large Output Voltage Swing: +14.1 V/ -14.6 V
- ESD Diodes Provided on the Inputs

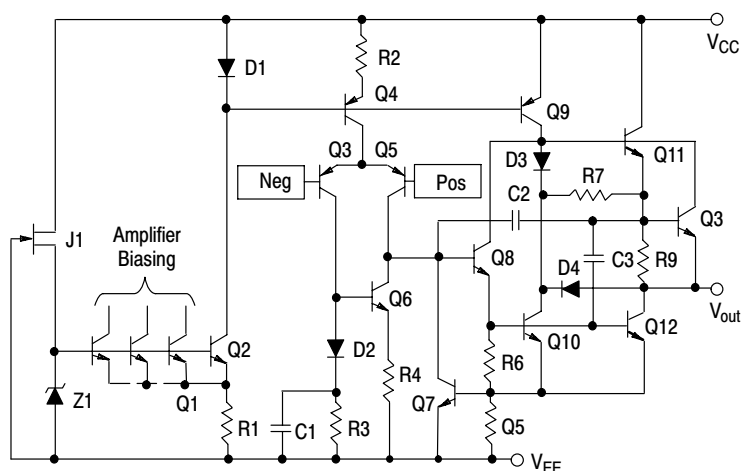


Figure 1. Representative Schematic Diagram
(Each Amplifier)

<http://onsemi.com>

MARKING DIAGRAMS

DUAL

8
1
PDIP-8
P SUFFIX
CASE 626

8
1
SO-8
D SUFFIX
CASE 751

QUAD

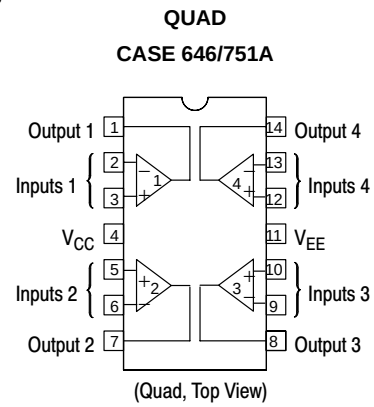
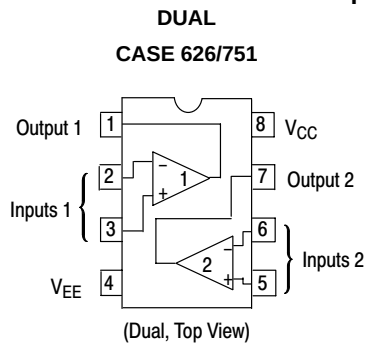
1
14
PDIP-14
P SUFFIX
CASE 646

SO-14
D SUFFIX
CASE 751A

A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week

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PIN CONNECTIONS



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Supply Voltage (V_{CC} to V_{EE})	V_S	+36	V
Input Differential Voltage Range	V_{IDR}	Note 1.	V
Input Voltage Range	V_{IR}	Note 1.	V
Output Short Circuit Duration (Note 2.)	t_{SC}	Indefinite	sec
Maximum Junction Temperature	T_J	+150	°C
Storage Temperature	T_{stg}	-60 to +150	°C
Maximum Power Dissipation	P_D	Note 2.	mW

1. Either or both input voltages must not exceed the magnitude of V_{CC} or V_{EE} .
2. Power dissipation must be considered to ensure maximum junction temperature (T_J) is not exceeded (see Figure 2).

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DC ELECTRICAL CHARACTERISTICS ($V_{CC} = +15\text{ V}$, $V_{EE} = -15\text{ V}$, $T_A = 25^\circ\text{C}$, unless otherwise noted.)

Characteristics	Symbol	Min	Typ	Max	Unit
Input Offset Voltage ($R_S = 10\ \Omega$, $V_{CM} = 0\text{ V}$, $V_O = 0\text{ V}$) (MC33078) $T_A = +25^\circ\text{C}$ $T_A = -40^\circ$ to $+85^\circ\text{C}$ (MC33079) $T_A = +25^\circ\text{C}$ $T_A = -40^\circ$ to $+85^\circ\text{C}$	$ V_{IO} $	– – – –	0.15 – 0.15 –	2.0 3.0 2.5 3.5	mV
Average Temperature Coefficient of Input Offset Voltage $R_S = 10\ \Omega$, $V_{CM} = 0\text{ V}$, $V_O = 0\text{ V}$, $T_A = T_{low}$ to T_{high}	$\Delta V_{IO}/\Delta T$	–	2.0	–	$\mu\text{V}/^\circ\text{C}$
Input Bias Current ($V_{CM} = 0\text{ V}$, $V_O = 0\text{ V}$) $T_A = +25^\circ\text{C}$ $T_A = -40^\circ$ to $+85^\circ\text{C}$	I_{IB}	– –	300 –	750 800	nA
Input Offset Current ($V_{CM} = 0\text{ V}$, $V_O = 0\text{ V}$) $T_A = +25^\circ\text{C}$ $T_A = -40^\circ$ to $+85^\circ\text{C}$	I_{IO}	– –	25 –	150 175	nA
Common Mode Input Voltage Range ($\Delta V_{IO} = 5.0\text{ mV}$, $V_O = 0\text{ V}$)	V_{ICR}	± 13	± 14	–	V
Large Signal Voltage Gain ($V_O = \pm 10\text{ V}$, $R_L = 2.0\text{ k}\Omega$) $T_A = +25^\circ\text{C}$ $T_A = -40^\circ$ to $+85^\circ\text{C}$	A_{VOL}	90 85	110 –	– –	dB
Output Voltage Swing ($V_{ID} = \pm 1.0\text{ V}$) $R_L = 600\ \Omega$ $R_L = 600\ \Omega$ $R_L = 2.0\text{ k}\Omega$ $R_L = 2.0\text{ k}\Omega$ $R_L = 10\text{ k}\Omega$ $R_L = 10\text{ k}\Omega$	V_{O+} V_{O-} V_{O+} V_{O-} V_{O+} V_{O-}	– – +13.2 – +13.5 –	+10.7 –11.9 +13.8 –13.7 +14.1 –14.6	– – – –13.2 – –14	V
Common Mode Rejection ($V_{in} = \pm 13\text{ V}$)	CMR	80	100	–	dB
Power Supply Rejection (Note 3.) $V_{CC}/V_{EE} = +15\text{ V}/-15\text{ V}$ to $+5.0\text{ V}/-5.0\text{ V}$	PSR	80	105	–	dB
Output Short Circuit Current ($V_{ID} = 1.0\text{ V}$, Output to Ground) Source Sink	I_{SC}	+15 –20	+29 –37	– –	mA
Power Supply Current ($V_O = 0\text{ V}$, All Amplifiers) (MC33078) $T_A = +25^\circ\text{C}$ $T_A = -40^\circ$ to $+85^\circ\text{C}$ (MC33079) $T_A = +25^\circ\text{C}$ $T_A = -40^\circ$ to $+85^\circ\text{C}$	I_D	– – – –	4.1 – 8.4 –	5.0 5.5 10 11	mA

3. Measured with V_{CC} and V_{EE} differentially varied simultaneously.

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AC ELECTRICAL CHARACTERISTICS ($V_{CC} = +15\text{ V}$, $V_{EE} = -15\text{ V}$, $T_A = 25^\circ\text{C}$, unless otherwise noted.)

Characteristics	Symbol	Min	Typ	Max	Unit
Slew Rate ($V_{in} = -10\text{ V to } +10\text{ V}$, $R_L = 2.0\text{ k}\Omega$, $C_L = 100\text{ pF}$, $A_V = +1.0$)	SR	5.0	7.0	—	V/ μs
Gain Bandwidth Product ($f = 100\text{ kHz}$)	GBW	10	16	—	MHz
Unity Gain Bandwidth (Open Loop)	BW	—	9.0	—	MHz
Gain Margin ($R_L = 2.0\text{ k}\Omega$ $C_L = 0\text{ pF}$ $C_L = 100\text{ pF}$)	A_m	— —	-11 -6.0	— —	dB
Phase Margin ($R_L = 2.0\text{ k}\Omega$ $C_L = 0\text{ pF}$ $C_L = 100\text{ pF}$)	ϕ_m	— —	55 40	— —	Deg
Channel Separation ($f = 20\text{ Hz to } 20\text{ kHz}$)	CS	—	-120	—	dB
Power Bandwidth ($V_O = 27\text{ V}_{pp}$, $R_L = 2.0\text{ k}\Omega$, $\text{THD} \leq 1.0\%$)	BW_p	—	120	—	kHz
Total Harmonic Distortion ($R_L = 2.0\text{ k}\Omega$, $f = 20\text{ Hz to } 20\text{ kHz}$, $V_O = 3.0\text{ V}_{rms}$, $A_V = +1.0$)	THD	—	0.002	—	%
Open Loop Output Impedance ($V_O = 0\text{ V}$, $f = 9.0\text{ MHz}$)	$ Z_O $	—	37	—	Ω
Differential Input Resistance ($V_{CM} = 0\text{ V}$)	R_{in}	—	175	—	k Ω
Differential Input Capacitance ($V_{CM} = 0\text{ V}$)	C_{in}	—	12	—	pF
Equivalent Input Noise Voltage ($R_S = 100\text{ }\Omega$, $f = 1.0\text{ kHz}$)	e_n	—	4.5	—	nV/ $\sqrt{\text{Hz}}$
Equivalent Input Noise Current ($f = 1.0\text{ kHz}$)	i_n	—	0.5	—	pA/ $\sqrt{\text{Hz}}$

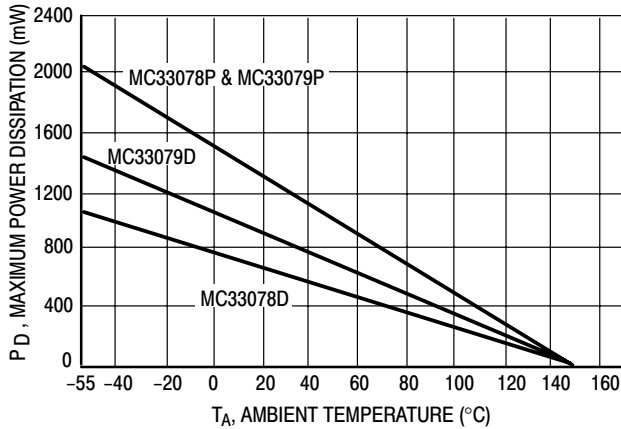


Figure 2. Maximum Power Dissipation versus Temperature

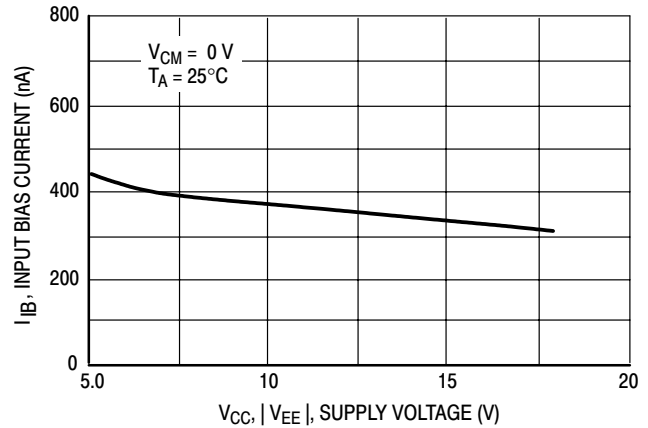


Figure 3. Input Bias Current versus Supply Voltage

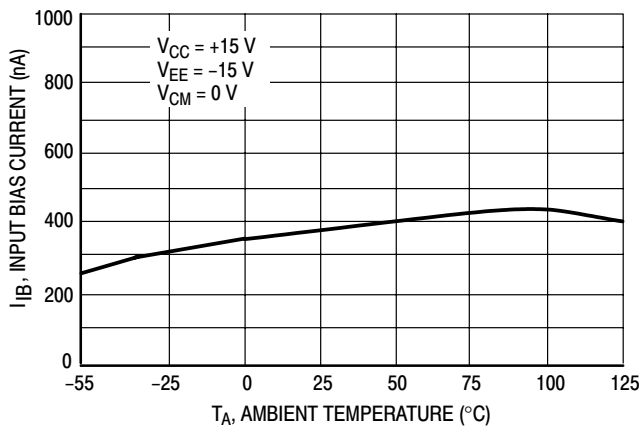


Figure 4. Input Bias Current versus Temperature

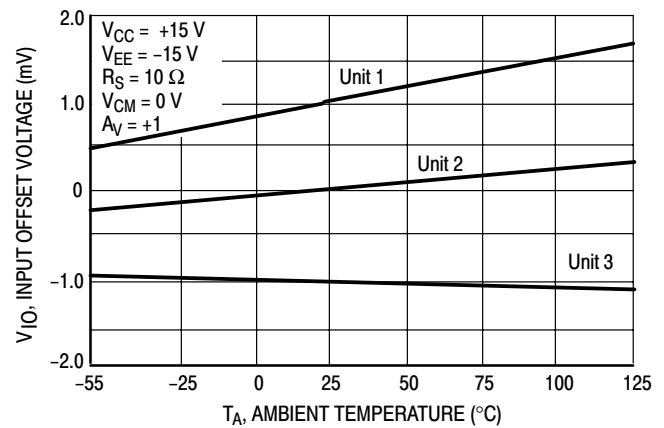


Figure 5. Input Offset Voltage versus Temperature

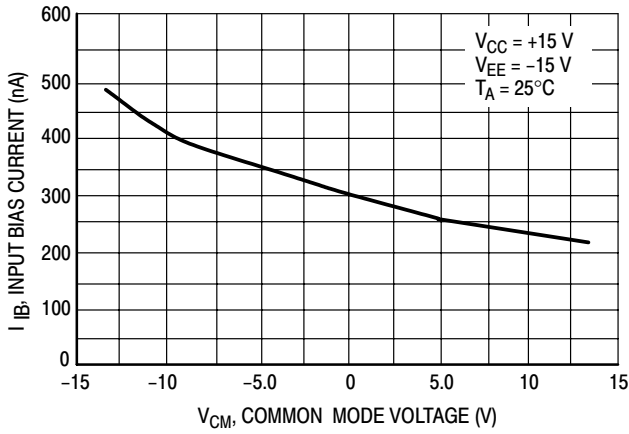


Figure 6. Input Bias Current versus Common Mode Voltage

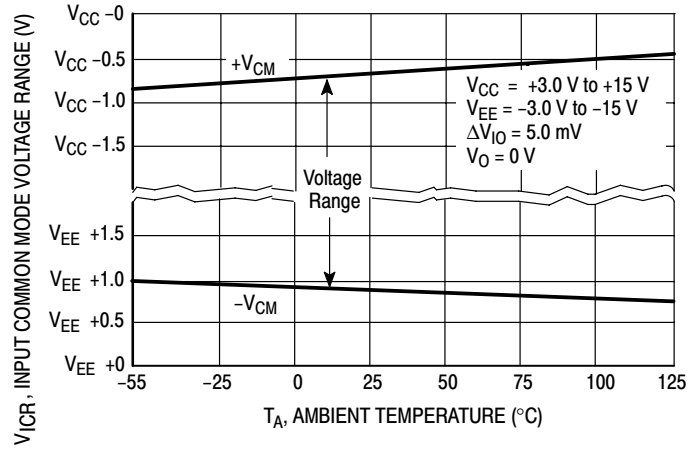


Figure 7. Input Common Mode Voltage Range versus Temperature

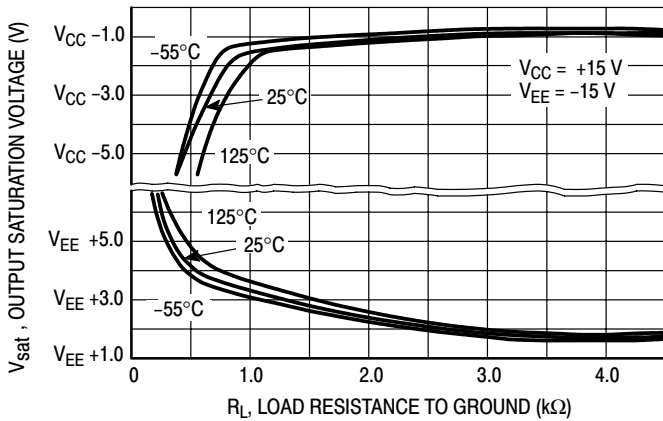


Figure 8. Output Saturation Voltage versus Load Resistance to Ground

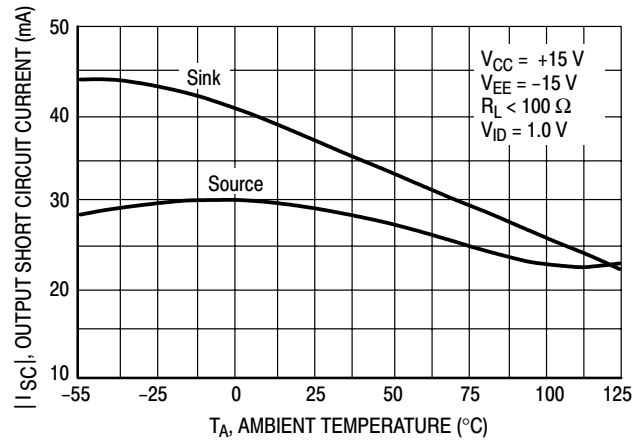


Figure 9. Output Short Circuit Current versus Temperature

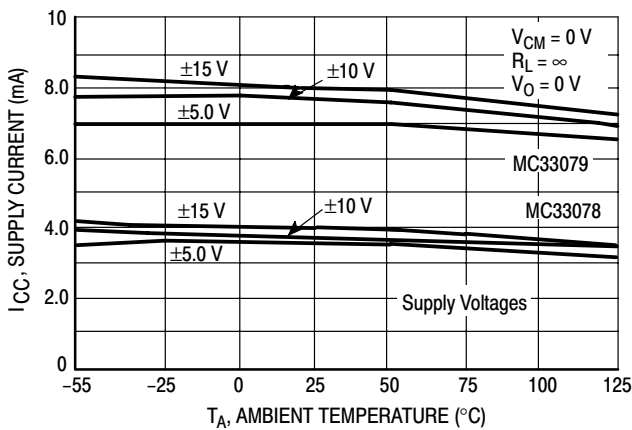


Figure 10. Supply Current versus Temperature

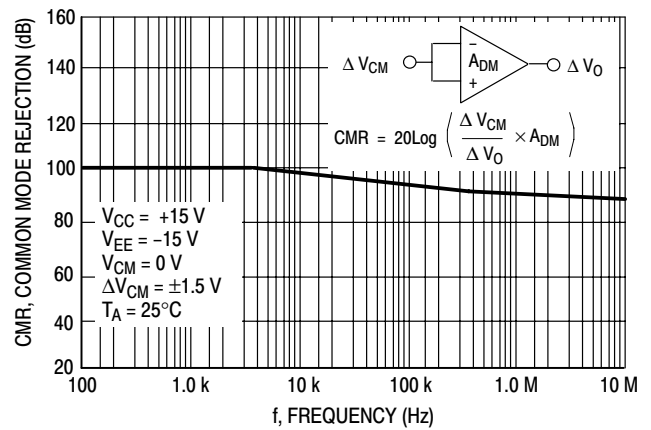


Figure 11. Common Mode Rejection versus Frequency

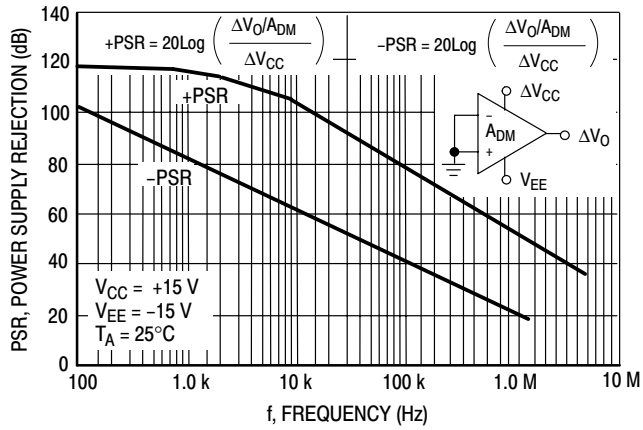


Figure 12. Power Supply Rejection versus Frequency

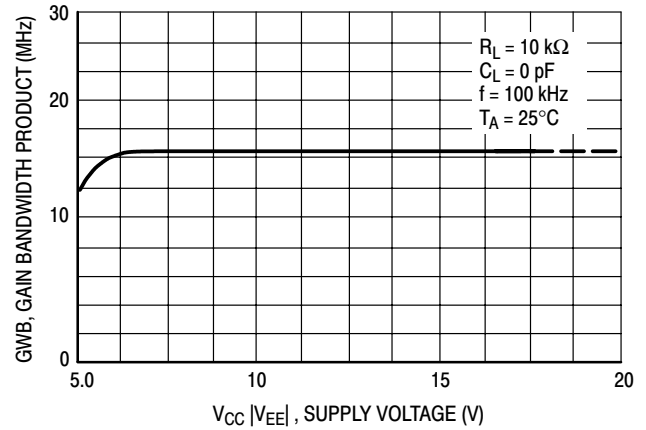


Figure 13. Gain Bandwidth Product versus Supply Voltage

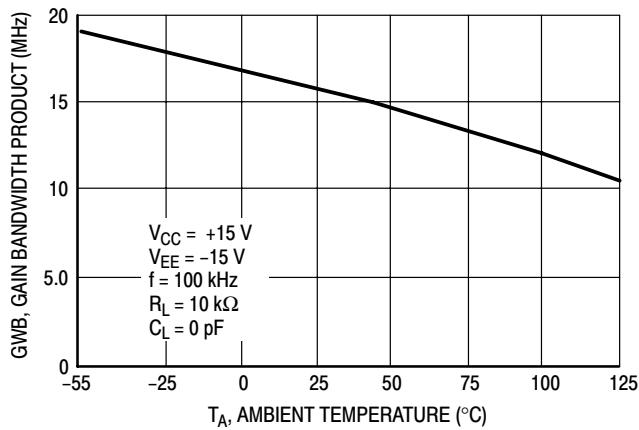


Figure 14. Gain Bandwidth Product versus Temperature

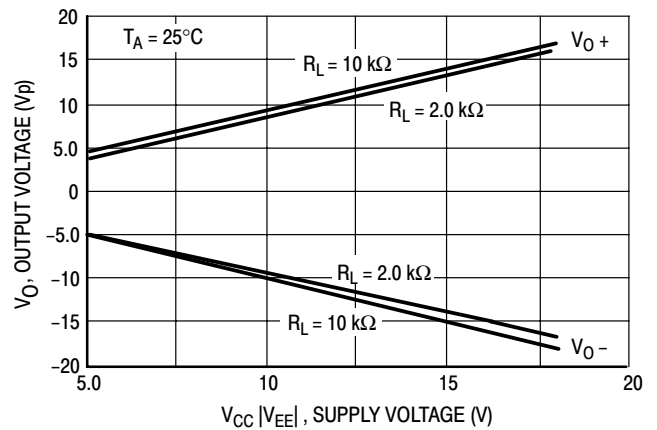


Figure 15. Maximum Output Voltage versus Supply Voltage

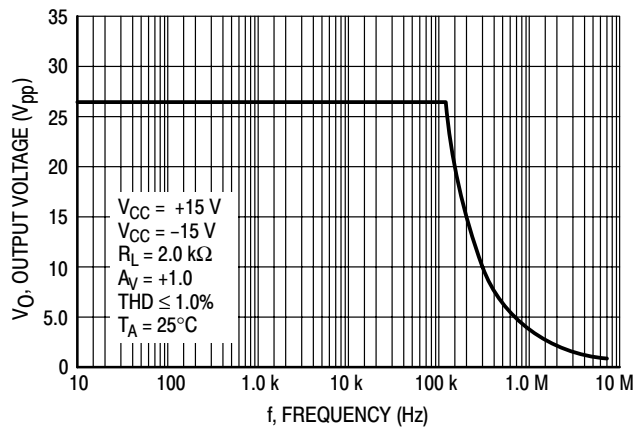


Figure 16. Output Voltage versus Frequency

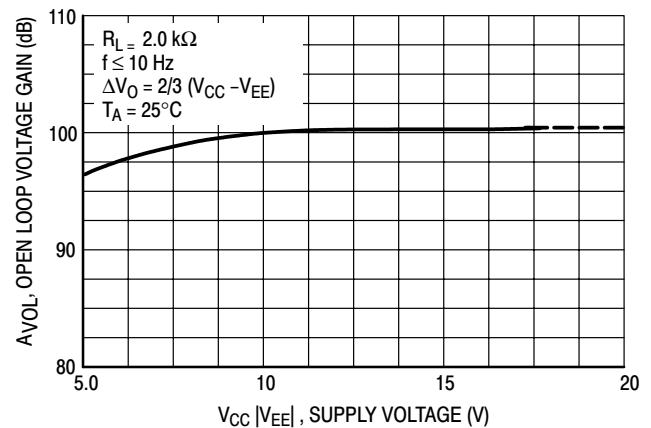


Figure 17. Open Loop Voltage Gain versus Supply Voltage

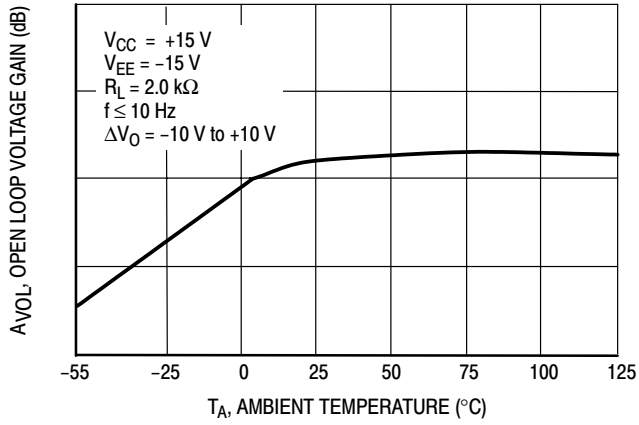


Figure 18. Open Loop Voltage Gain versus Temperature

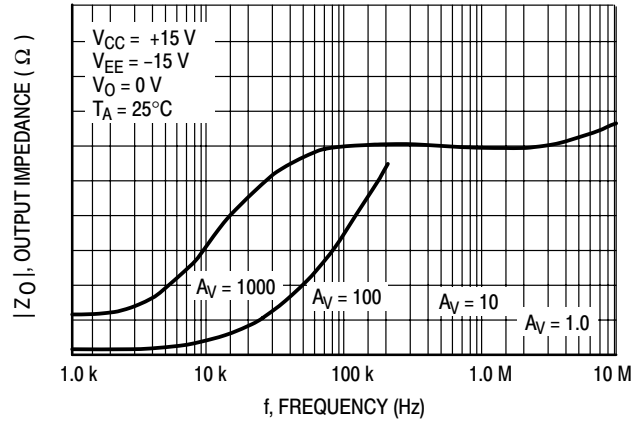


Figure 19. Output Impedance versus Frequency

Figure 20. Channel Separation versus Frequency

Figure 21. Total Harmonic Distortion versus Frequency

Figure 22. Total Harmonic Distortion versus Output Voltage

Figure 23. Slew Rate versus Supply Voltage

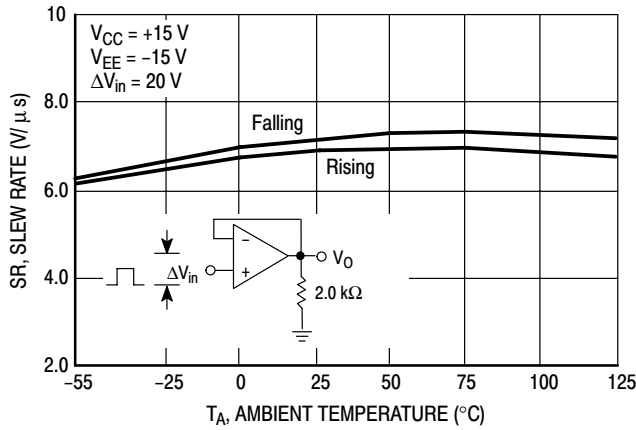


Figure 24. Slew Rate versus Temperature

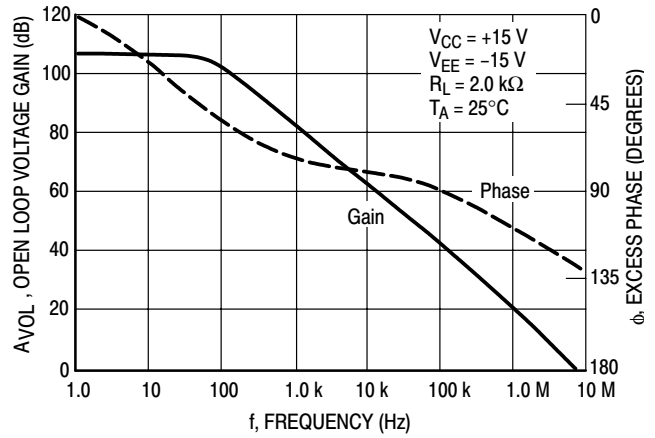


Figure 25. Voltage Gain and Phase versus Frequency

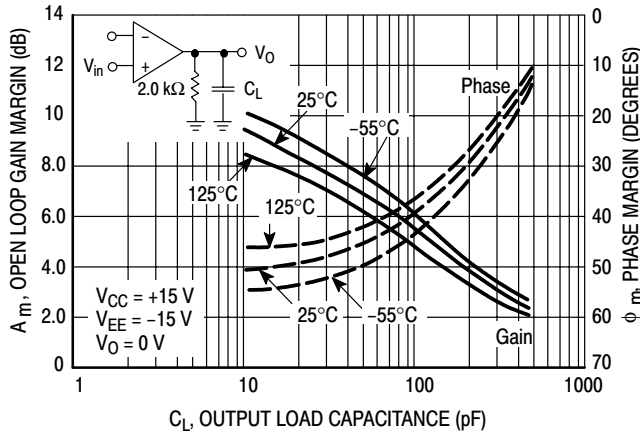


Figure 26. Open Loop Gain Margin and Phase Margin versus Load Capacitance

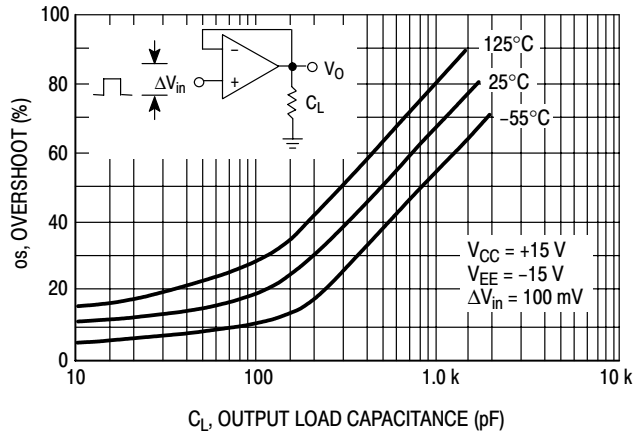


Figure 27. Overshoot versus Output Load Capacitance

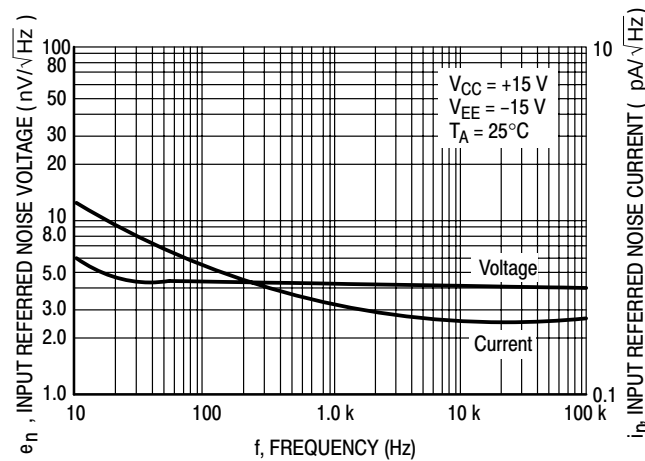


Figure 28. Input Referred Noise Voltage and Current versus Frequency

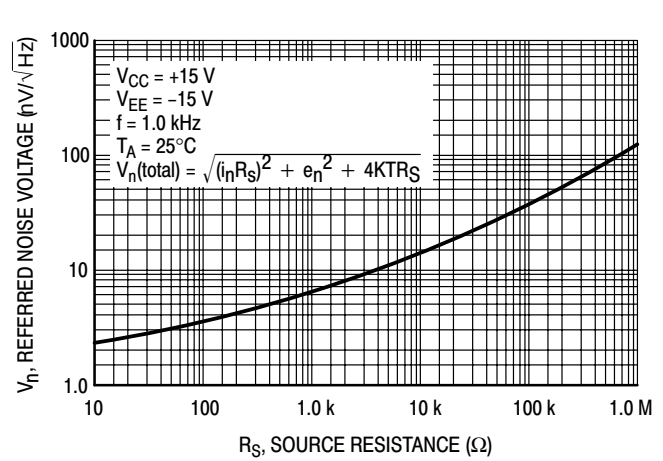


Figure 29. Total Input Referred Noise Voltage versus Source Resistance

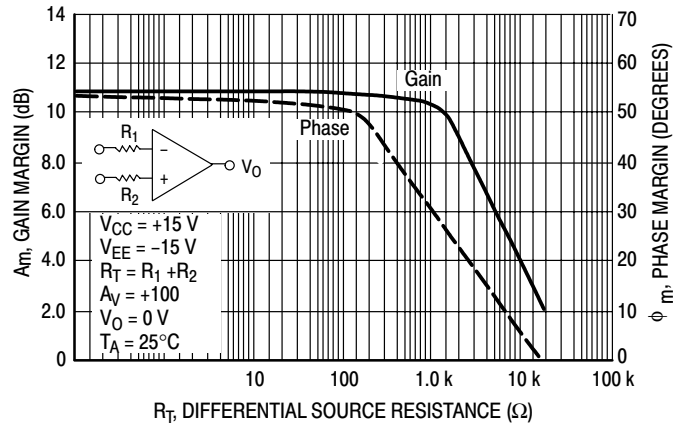


Figure 30. Phase Margin and Gain Margin versus Differential Source Resistance

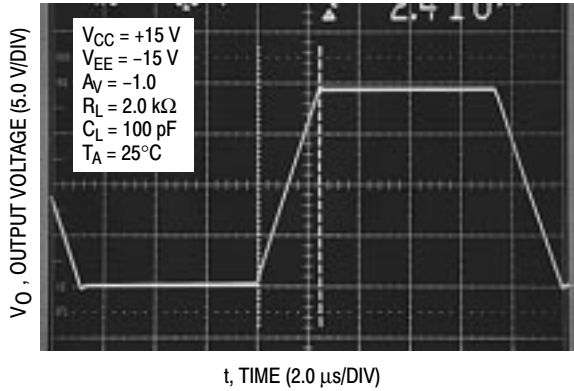


Figure 31. Inverting Amplifier Slew Rate

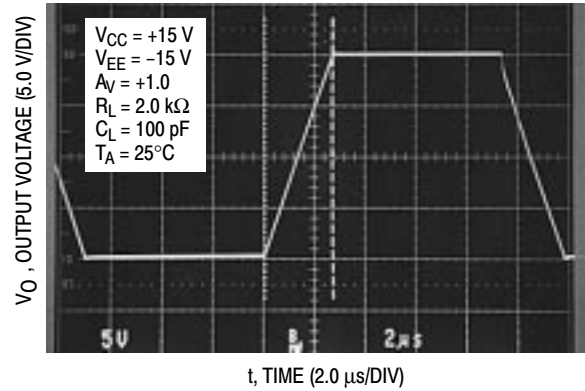


Figure 32. Non-inverting Amplifier Slew Rate

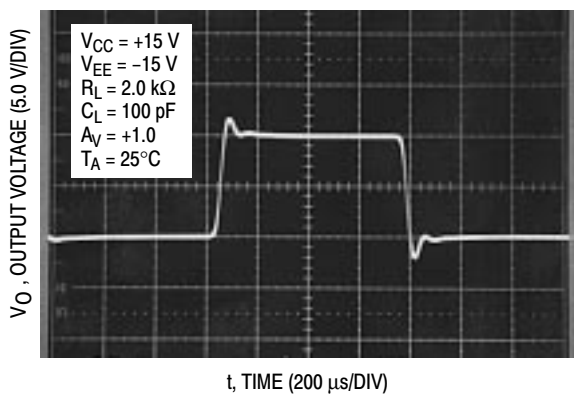


Figure 33. Non-inverting Amplifier Overshoot

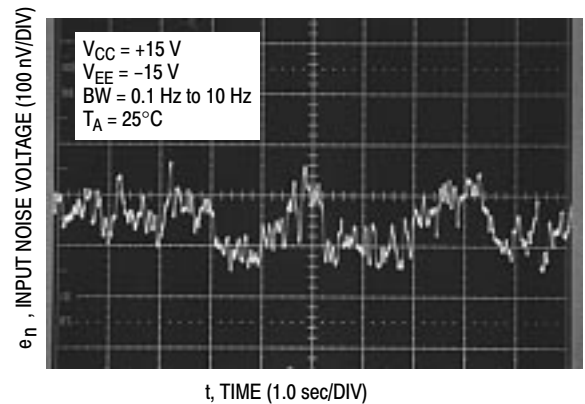
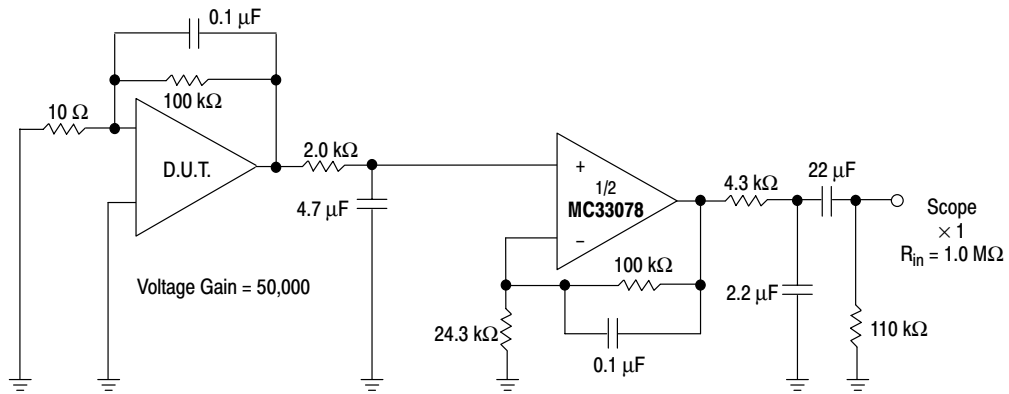


Figure 34. Low Frequency Noise Voltage versus Time

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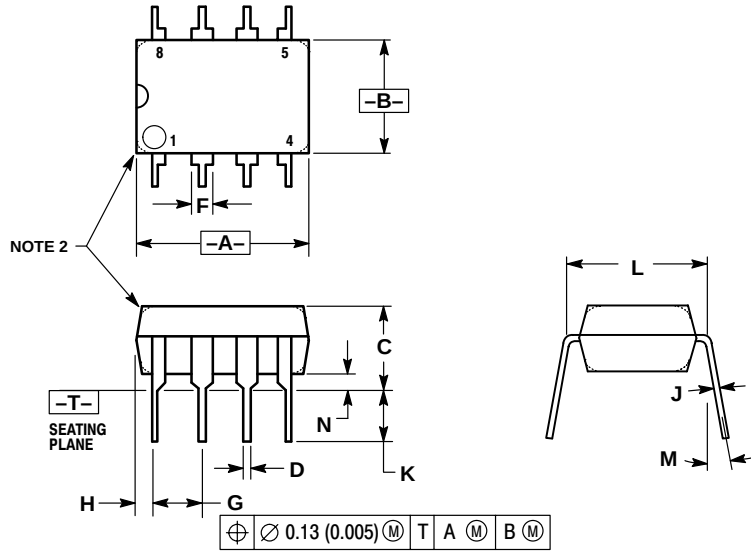
Note: All capacitors are non-polarized.

**Figure 35. Voltage Noise Test Circuit
(0.1 Hz to 10 Hz_{p-p})**

MC33078, MC33079

PACKAGE DIMENSIONS

PDIP-8
P SUFFIX
CASE 626-05
ISSUE L

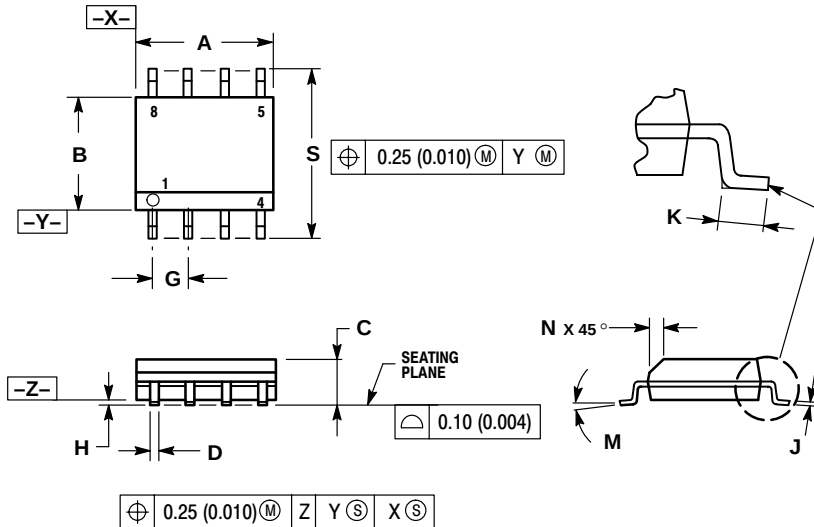


NOTES:

1. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
2. PACKAGE CONTOUR OPTIONAL (ROUND OR SQUARE CORNERS).
3. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	9.40	10.16	0.370	0.400
B	6.10	6.60	0.240	0.260
C	3.94	4.45	0.155	0.175
D	0.38	0.51	0.015	0.020
F	1.02	1.78	0.040	0.070
G	2.54 BSC		0.100 BSC	
H	0.76	1.27	0.030	0.050
J	0.20	0.30	0.008	0.012
K	2.92	3.43	0.115	0.135
L	7.62 BSC		0.300 BSC	
M	10°		10°	
N	0.76	1.01	0.030	0.040

SO-8
D SUFFIX
CASE 751-07
ISSUE W



NOTES:

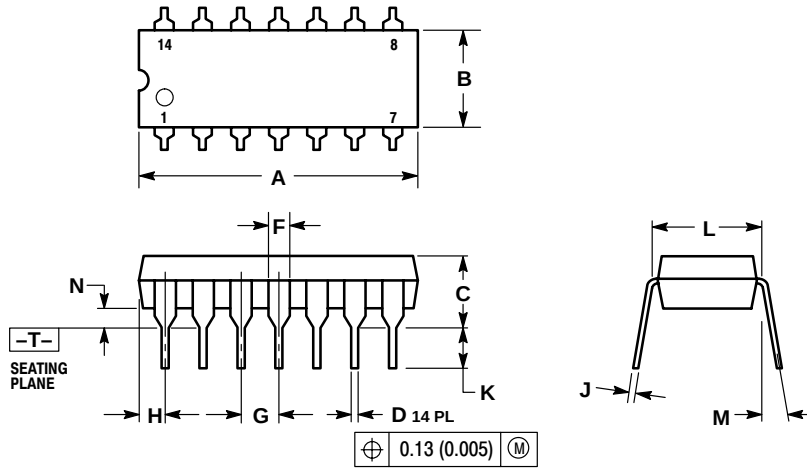
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°		8°	
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

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PACKAGE DIMENSIONS

PDIP-14
P SUFFIX
CASE 646-06
ISSUE M

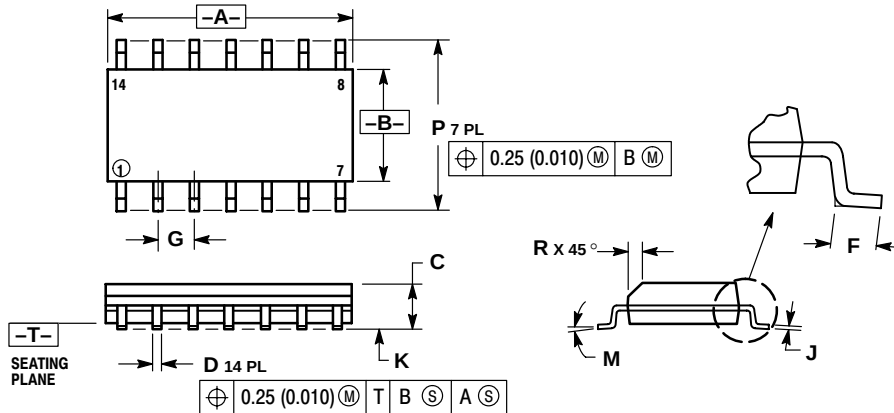


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.715	0.770	18.16	18.80
B	0.240	0.260	6.10	6.60
C	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100 BSC		2.54 BSC	
H	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.290	0.310	7.37	7.87
M	---	10°	---	10°
N	0.015	0.039	0.38	1.01

SO-14
D SUFFIX
CASE 751A-03
ISSUE F



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

Notes

Notes

Notes

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German Phone: (+1) 303-308-7140 (Mon-Fri 2:30pm to 7:00pm CET)
Email: ONlit-german@hibbertco.com
French Phone: (+1) 303-308-7141 (Mon-Fri 2:00pm to 7:00pm CET)
Email: ONlit-french@hibbertco.com
English Phone: (+1) 303-308-7142 (Mon-Fri 12:00pm to 5:00pm GMT)
Email: ONlit@hibbertco.com

EUROPEAN TOLL-FREE ACCESS*: 00-800-4422-3781

*Available from Germany, France, Italy, UK, Ireland

CENTRAL/SOUTH AMERICA:

Spanish Phone: 303-308-7143 (Mon-Fri 8:00am to 5:00pm MST)
Email: ONlit-spanish@hibbertco.com
Toll-Free from Mexico: Dial 01-800-288-2872 for Access –
then Dial 866-297-9322

ASIA/PACIFIC: LDC for ON Semiconductor – Asia Support

Phone: 303-675-2121 (Tue-Fri 9:00am to 1:00pm, Hong Kong Time)
Toll Free from Hong Kong & Singapore:
001-800-4422-3781
Email: ONlit-asia@hibbertco.com

JAPAN: ON Semiconductor, Japan Customer Focus Center

4-32-1 Nishi-Gotanda, Shinagawa-ku, Tokyo, Japan 141-0031
Phone: 81-3-5740-2700
Email: r14525@onsemi.com

ON Semiconductor Website: <http://onsemi.com>

For additional information, please contact your local Sales Representative.